

	Document ID	Issue Date	Pages	Title
1	US 6549554 B2	20030415	19	Semiconductor laser element, semiconductor etchant, and method of fabricating the semiconductor laser element
2	US 6545296 B1	20030408	10	Semiconductor light emitting device
3	US 6472691 B2	20021029	13	Distributed feedback semiconductor laser device
4	US 6472679 B1	20021029	60	Semiconductor structures using a group III-nitride quaternary material system with reduced phase separation and method of fabrication
5	US 6377597 B1	20020423	22	Gallium nitride semiconductor light emitting element with active layer having multiplex quantum well structure and semiconductor laser light source device
6	US 6232623 B1	20010515	14	Semiconductor device on a sapphire substrate
7	US 5976904 A	19991102	13	Method of manufacturing semiconductor device
8	US 5960020 A	19990928	16	Semiconductor laser diode including ridge and partially disordered active layer

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5	372/45
6	257/103
7	438/33
8	372/46

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	1854	laser and gaas and (ridge mesa) and electrode	USPAT; EPO; JPO; DERWENT; IBM_TD	2003/06/05 12:24
2	BRS	L2	663	1 and 257/\$.ccls.	USPAT; EPO; JPO; DERWENT; IBM_TD	2003/06/05 12:25
3	BRS	L35	145	438/39.cccls. and @ay<2001	USPAT; EPO; JPO; DERWENT; IBM_TD	2003/06/05 13:43
4	BRS	L36	493	438/40.cccls. and @ay<2001	USPAT; EPO; JPO; DERWENT; IBM_TD	2003/06/05 13:43

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9	US 5939733 A	19990817	12	Compound semiconductor device having a group III-V compound semiconductor layer containing therein Tl and As
10	US 5892785 A	19990406	13	Semiconductor laser
11	US 5550393 A	19960827	19	Semiconductor layer structure having distributed strain and optical semiconductor device including such strained layer
12	US 5388117 A	19950207	25	Polarization insensitive semiconductor optical amplifier and an optical communication system using the same
13	US 5260588 A	19931109	10	Light-emitting diode array
14	US 4958202 A	19900918	13	Semiconductor light-emitting device and method of manufacturing the same
15	US 4719498 A	19880112	17	Optoelectronic integrated circuit

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16	US 4142160 A	19790227	13	Hetero-structure injection laser

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